IWGO 2026 Program Overview

Room /Time	ESJ Concourse	ESJ 0202
MoM		IWGO-MoM1: Plenary Session I IWGO-MoM2: Epitaxial Growth and Doping Control I
MoA		IWGO-MoA1: Defects Science I IWGO-MoA2: Defects Science II
MoP	Poster Sessions	
TuM		IWGO-TuM1: Substrate Development and Material Quality I IWGO-TuM2: Substrate Development and Material Quality II
TuA		IWGO-TuA1: Heterogeneous Integration and other WBG and UWBG Oxides Beyond Ga_2O_3 IWGO-TuA2: Defects Science III & Thermal Management
TuP	Poster Sessions	
WeM		IWGO-WeM1: Plenary Session II IWGO-WeM2: Epitaxial Growth and Doping Control II
WeA		IWGO-WeA: Advanced Device Scaling and Fabrication Techniques I
WeP	Poster Sessions	Rump Session (6:00 – 8:00 pm)
ThM		IWGO-ThM1: Theory, Modeling, and Simulation IWGO-ThM2: Defects Science IV
ThA	Offsite Excursion	
FrM		IWGO-FrM1: Plenary Session III IWGO-FrM2: Advanced Device Scaling and Fabrication Techniques II

Monday Morning, August 3, 2026

	Room ESJ 0202	
8:00am	**BREAKFAST**	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-MoM1** **Plenary Session I** **Moderator:** **Marko Tadjer**, U.S. Naval Research Laboratory
8:45am	Welcome & Sponsor Thank Yous	
9:00am	**INVITED: IWGO-MoM1-13** PLENARY: Single Crystals and Wafers of β-Ga_2O_3, β-$(Al_xGa_{1-x})_2O_3$, and r-GeO2, ***Zbigniew Galazka***, Leibniz-Institut für Kristallzüchtung, Germany	
9:45am	**INVITED: IWGO-MoM1-22** Plasma-Treatment Based (Near) Surface Doping of Semiconducting Oxides, ***Oliver Bierwagen***, Paul-Drude Institute for Solid State Electronics, Germany; *Piero Mazzolini,* University of Parma, Italy	
10:10am	**INVITED: IWGO-MoM1-27** Lattice Defects in β-Ga_2O_3 Crystals and Power Devices, *Yongzhao Yao*, ***Yukari Ishikawa,*** Mie University, Japan	
10:35am	**BREAK & EXHIBITS**	
11:05am	**INVITED: IWGO-MoM2-38** Toward 150mm Ga2O3 Epitaxy by HVPE, ***Jacob Leach***, *Caroline Reilly, Heather Splawn,* KYMA TECHNOLOGIES, INC	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-MoM2** **Epitaxial Growth and Doping Control I** **Moderators:** **Oliver Bierwagen**, Paul-Drude Institute for Solid State Electronics, Germany, **Yuichi Oshima**, National Institute for Materials Science, Japan
11:30am	**IWGO-MoM2-43** MOCVD Growth of (011) β-Ga_2O_3 up to 20 µm: Defect Optimization and Device Impact, ***Md Mosarof Hossain Sarkar (Student)***, *Dong su Yu,* The Ohio State University; *Jiawei Liu*, SUNY at Buffalo; *Sadikul Alam, Mehidi Hassan,* The Ohio State University; *Yuki Ueda, Chia-Hung Lin, Kohei Sasaki,* Novel Crystal Technology, Japan; *Jinwoo Hwang,* The Ohio State University; *Uttam Singisetti,* SUNY at Buffalo; *Hongping Zhao,* The Ohio State University	
11:45am	**IWGO-MoM2-46** Colossal Bandgaps: Growing Si-Doped α-(AlxGa1-x)$_2O_3$ Films with Eg ≤ 7 eV with s-MBE, ***Jacob Steele (Student)***, *Debaditya Bhattacharya, Kazuki Nomoto,* Cornell University; *M. K. Indika Senevirathna,* Clark Atlanta University; *Huili "Grace" Xing, Debdeep Jena, Darrell G. Schlom,* Cornell University	
12:00pm	**IWGO-MoM2-49** Fast Step-Flow Growth on Highly Offcut (100) Ga2O3 Substrates, ***M Brooks Tellekamp***, National Renewable Energy Laboratory; *Drew Haven, David Joyce,* Luxium Solutions; *Henry Garland, John Mangum,* National Renewable Energy Laboratory; *Kevin Schulte, Anna Sacchi, Matthew Young, Andriy Zakutayev,* national renewable Energy Laboratory	
12:15pm	**IWGO-MoM2-52** Record High Mobility with Observation of Quantum Oscillations at Low Temperature for 2DEGs in MOCVD Grown β-$(Al_xGa_{1-x})_2O_3$/β-Ga_2O_3 Heterostructures, ***Joshua Buontempo (Student)***, *Cameron Gorsak, Pushpanshu Tripathi, Hari Nair,* Cornell University	

Monday Afternoon, August 3, 2026

	Room ESJ 0202	
2:00pm	**INVITED: IWGO-MoA1-1** Toward Quantitative Modeling of Temperature-Dependent Defect Physics in β-Ga_2O_3, ***Elif Ertekin***, University of Illinois; *Michael Scarpulla,* University of Utah; *Joel Varley,* Lawrence Livermore National Lab; *Nasim Alem,* Penn State University; *Channyung Lee, Grace McKnight,* University of Illinois; *Aaditta Arnab,* University of Utah	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-MoA1** **Defects Science I** **Moderator:** **Darshana Wickramaratne**, Naval Research Laboratory
2:25pm	**IWGO-MoA1-6** Characterization of β-Ga_2O_3 Deep Acceptor/n^- Junction Diodes Grown by Molecular Beam Epitaxy, ***Steve Rebollo (Student)***, *Wolfgang Buchmaier, Sriram Krishnamoorthy, James Speck,* UC Santa Barbara	
2:40pm	**IWGO-MoA1-9** Identification and Suppression of Carbon-Related Trap States and Carrier Compensation in MOCVD-Grown β-Ga_2O_3, ***Miranda Carver (Student)***, *Hemant Ghadi, Lingyu Meng, Dong Su Yu, Hongping Zhao, Aaron Arehart, Steven Ringel,* Ohio State University	
2:55pm	**IWGO-MoA1-12** Deep Trap States in Mg/N Co-Implanted β-Ga_2O_3 Current Blocking Layers Revealed by Thermally Stimulated Current Spectroscopy, ***Hitoshi Takane***, *Yusuke Yamashita,* Toyota Central R&D Labs., Inc., Japan; *Fenfen Fenda Florena, Hironobu Miyamoto, Kohei Sasaki,* Novel Crystal Technology, Inc., Japan; *Daigo Kikuta,* Toyota Central R&D Labs., Inc., Japan	
3:10pm	**IWGO-MoA1-15** Effects of 230 MeV Ca Swift Heavy Ion Irradiation on β-Ga_2O_3 Schottky Diodes, ***Yanzhen Zhao (Student)***, Ohio State University; *Cale Overstreet,* University of Tennessee, Knoxville; *Hemant Ghadi, Quentin Shuai,* Ohio State University; *Kay-Obbe Voss,* GSI Helmholtz Centre For Heavy Ion Research; *Maik Lang,* University of Tennessee, Knoxville; *Steven Ringel, Aaron Arehart,* Ohio State University	
3:25pm	**IWGO-MoA1-18** Machine Learning Quantification of Dislocation Defects in Ga_2O_3 Using X-Ray Topography, ***James Gallagher***, NRL; *Christian Reimann,* Rigaku, Germany; *Caroline Reilly, Jacob Leach, Heather Splawn,* Kyma Technologies; *Nadeemullah Mahadik, Marko Tadjer, Karl Hobart, Michael Mastro,* NRL	
3:40pm	**BREAK & EXHIBITS**	
4:10pm	**INVITED: IWGO-MoA2-27** Advancing Understanding in Conductivity Control in Ga2O3 Polymorphs and Alloys Through Atomistic Simulations, ***Joel Varley***, Lawrence Livermore National Laboratory	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-MoA2** **Defects Science II** **Moderators:** **Emmanouil Kioupakis**, University of Michigan, **Hartwin Peelaers**, University of Kansas
4:35pm	**IWGO-MoA2-32** High-Throughput, High-Resolution, Three-DimensionalObservationof Threading Dislocations in β-Ga2O3 Using Phase-Contrast Microscopy, ***Yukari Ishikawa***, *Daiki Katsube,* Japan Fine Ceramics Center, Japan; *Yongzaho Yao,* Mie Univ., Japan Fine Ceramics Center, Japan; *Koji Sato,* Japan Fine Ceramices Center, Japan; *Kohei Sasaki,* Novel Crystal Technology, Japan	
4:50pm	**IWGO-MoA2-35** Origin of Donor Compensation in $(Al_xGa_{(1-x)})_2O_3$ Alloys, ***Sierra Seacat***, *Hartwin Peelaers,* University of Kansas	
5:05pm	**IWGO-MoA2-38** Photoemission Electron Microscopy for Imaging Defects, *Andrew Winchester, Min-Yeong Kim, Ory Maimon,* National Institute for Science and Technology (NIST); *Dinusha Mudiyanselage, Houqiang Fu,* Arizona State University; *Sang-Mo Koo,* Kwangwoon University, Republic of Korea; *Qiliang Li,* George Mason University; ***Sujitra Pookpanratana***, National Institute for Science and Technology (NIST)	

International Workshop on Gallium Oxide and Related Materials (IWGO-6)
Room ESJ Concourse - Session IWGO-MoPI
Invited Poster Session
5:20 – 5:35 pm

IWGO-MoPI-1
INVITED POSTER: Reliability of Ga_2O_3 Schottky Barrier Diodes, ***Md Hafijur Rahman (Student)***, *Nahid Al-Mamun,* Penn State University*; Jian-Sian LI,* University of Florida, Gainesville*; Aman Haque, Douglas E. Wolfe,* Penn State University*; Fan Ren,* University of Florida, Gainesville

IWGO-MoPI-2
INVITED POSTER: Single-Event Transient Study of Ga_2O_3 Rectifiers, ***Ani Khachatrian***, US Naval Research Laboratory*; Stephen Pearton, Fan Ren,* University of Florida*; Joel Hales,* Amentum*; Dale McMorrow,* US Naval Research Laboratory

IWGO-MoPI-3
INVITED POSTER: Nitrogen Precursor Selection for Controllable Doping in MOCVD Ga_2O_3, *William Brand,* ***Fikadu Alema****, Andrei Osinsky,* Agnitron Technology

IWGO-MoPI-4 INVITED POSTER: Phase Transformation and Defect Evolution in Ge-Implanted β-Ga_2O_3(In Memory of Professor Stephen J. Pearton), ***Elaf Anber***, *Daniel Foley,* Johns Hopkins University*; Andrew C. Lang,* US Naval Research Laboratory*; James Nathaniel,* Johns Hopkins University*; James L Hart,* US Naval Research Laboratory*; Marko J Tadjer, Karl D. Hobart,* Naval Research Laboratory*; Stephen Pearton,* University of Florida*; Mitra Taheri,* Johns Hopkins University

IWGO-MoPI-5 INVITED POSTER: Prospect of Wide- and Ultrawide-Bandgap Semiconductors for Ultrahigh-Voltage Vertical Unipolar Power Switching, ***Franklin Nouketcha***, *Aivars Lelis, Daniel Habersat, Ronald Green,* DEVCOM Army Research Laboratory*; Neil Goldsman,* ECE Department, University of Maryland, College Park

International Workshop on Gallium Oxide and Related Materials (IWGO-6)

Room ESJ Concourse - Session IWGO-MoP

IWGO Poster Session I

Moderators:

Esmat Farzana, Iowa State University,

Katie Gann, Naval Research Laboratory

5:35 – 7:35 pm

IWGO-MoP-1

Anisotropic Wet Etching of β-Ga2O3 using TMAH, ***Takayoshi Oshima***, NIMS, Japan

IWGO-MoP-2

Electrical Characterization of 1D P–N Heterojunctions with Axial and Core–Shell Architectures, ***Roman Yatskiv***, Institute of Photonics and Electronics of the Czech Academy of Sciences, Czechia

IWGO-MoP-4

Metal-Catalyst-Dependent Growth of β-Ga_2O_3 Nanowires on Sapphire for Solar-Blind UV Photodetectors, ***JungBok Lee (Student)***, *MinSeok Jang, HeeJin Kim, JuEun An, HoJun Lee,* Pusan National University, Republic of Korea

IWGO-MoP-5

Epitaxial Growth of Si Doped β-$(InxGa1-x)_2O_3$ Thin Films on (010) β-Ga_2O_3 Substrates, ***Aoi Saito (Student)***, Kyoto Institute of Technology, Japan; *Hiroki Miyake,* MIRISE Technologies Corporation, Japan; *Hiroyuki Nishinaka,* Kyoto Institute of Technology, Japan

IWGO-MoP-6

Dependence of Substrate Orientation the β-Ga_2O_3 Single Crystal Layer Grown by the Flux Method, ***Kentaro Ishida (Student)***, *Toshinori Taishi,* Shinshu University, Japan

IWGO-MoP-7

Characterization of β-Ga2O3 Epitaxial Layers Using Time-Resolved Photoluminescence, ***Mahiro Ishikawa (Student)***, *Takuma Ishihara, Kazuki Shimazoe,* Nagoya Institute of Technology, Japan; *Kohei Sasaki,* Novel Crystal Technology, Japan; *Masashi Kato,* Nagoya Institute of Technology, Japan

IWGO-MoP-8

Crack-Free Dicing of β-Ga2O3 Substrates, ***Michael Liao***, APEX Microdevices; *Mark Goorsky,* University of California Los Angeles; *Piyush Shah,* APEX Microdevices

IWGO-MoP-9

Silicon Implantation Doping for Channel Definition of UID Alpha and Beta Ga_2O_3 Lateral MESFET Transistors, ***Aniol Vellvehí i Llovet (Student)***, Institut de microelectrònica de Barcelona (IMB-CNM-CSIC), Spain; *Amador Perez Tomas Perez Tomas,* Institut de Microelectrònica de Barcelona (IMB-CNM-CSIC), Spain

IWGO-MoP-10

Temperature-dependent Characteristics of HVPE-grown β-Ga_2O_3 Schottky Contacts with Different Metals, ***Eito Hatayama (Student)***, *Kazutaka Kanegae, Hajime Takayama, Michihiro Shintani, Hiroyuki Nishinaka,* Kyoto Institute of Technology, Japan

IWGO-MoP-11

Effect of Ion Charge and Implantation Dosage on Damage Recovery and Band Gap Narrowing in Sn-Implanted β-Ga_2O_3, ***Kishor Upadhyaya***, KAUST, Saudi Arabia; *D.M. Esteves, Marco Peres, Katharina Lorenz,* Instituto Superior Técnico, Portugal; *Iman Roqan,* KAUST, Saudi Arabia

IWGO-MoP-12

Electrical Stability of Cr_2O_3/β-Ga_2O_3 Heterojunction Diodes (HJDs) with Orientation-Dependent Breakdown Electric Field, ***Yizheng Liu (Student)***, *Haochen Wang, Carl Peterson, Chinmoy Saha, James Speck, Chris Van de Walle, Sriram Krishnamoorthy,* University of California at Santa Barbara

IWGO-MoP-14

NiO/Ga2O3 Heterojunction Rectifiers with Reverse Breakdown Voltage > 8.1 kV, *Hsiao-Hsuan Wan, Jian-Sian Li, Chao-Ching Chiang,* ***Katharina Loske (Student)***, *Travis Anderson,* University of Florida; *Aman Haque,* The Pennsylvania State University; *Marko Tadjer,* Naval Research Laboratory, USA; *Jacob Leach, Caroline Reilly,* Kyma Technologies; *Fan Ren,* University of Florida

IWGO-MoP-16

Multi-Kilovolt Vertical Nio/Ga_2O_3 P-N Heterojunction Diodes with Ring-Assisted Junction Termination Extension, ***Kanghee Shin (Student)***, Sejong University, Republic of Korea; *Ho Jung Jeon,* Seoul National University, Republic of Korea; *Jang Hyeok Park, Madani Labed, You Seung Rim,* Sejong University, Republic of Korea

IWGO-MoP-18

MOCVD-grown 12µm Thick Sn Doped (001) β-Ga_2O_3 Layers with Extremely Low Free Charge Concentrations, ***Akash Patnaik***, UVSQ – CNRS, France; *Corinne Sartel,* UVSQ – CNRS, France; *Yunlin Zheng,* INSP, Sorbonne Université, France; *Thomas Ribault, Yves Dumont, Ekaterine Chikoidze,* UVSQ – CNRS, France

IWGO-MoP-19

Structural Properties of Mist CVD Grown Rutile GeO_2 Thin Films on TiO_2 Substrates, ***Kazuki Shimazoe***, *Shota Ishiyama,* Nagoya Institute of Technology, Japan; *Hiroyuki Nishinaka,* Kyoto Institute of Technology, Japan; *Masashi Kato,* Nagoya Institute of Technology, Japan

IWGO-MoP-20

Epitaxy of b-$(AlxGa1-x)_2O_3$ on (001) b-Ga_2O_3 Substrates by MOCVD, ***Indraneel Sanyal***, AIXTRON Ltd., UK; *Dan Lamb, Ciaran Llewelyn, Shreyasi Maitra, Saptarsi Ghosh,* Swansea University, UK; *Andrew Pakes, K.B.K Teo,* AIXTRON Ltd., UK

IWGO-MoP-21

Performance Enhancement of β-Ga_2O_3 Deep-Ultraviolet Photodetectors via Al_2O_3 Passivation, ***Hee Won Shin (Student)***, *Jang Hyeok Park, You Seung Rim,* Sejong University, Republic of Korea; *Si-Young Bae,* Pukyong National University, Republic of Korea

IWGO-MoP-22

Suppression of Twin Nucleation in Bulk β-Ga_2O_3 Using Wide-Width Seeds, *Won-Jae LEE,* Dong-Eui University, Republic of Korea; ***Eun-Seo LEE (Student)***, Dong Eui University, Republic of Korea; *Eun-Jeong An, Sang-Jin Bae, Ho-Gyun Yun, Jung-Gon Kim, Kwang-Hee Jung, Mi-Seon Park,* Dong-Eui University, Republic of Korea; *Dong-Jin Lee, Jin-Ki Kang,* AXEL, Republic of Korea

IWGO-MoP-23

Comparison of NiO/β-Ga_2O_3 Heterojunction Diodes Fabricated Using Planar and Confocal RF Magnetron Sputtering Systems, ***Wojciech Hendzelek (Student)***, Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology- Institute of Microelectronics and Optoelectronics,, Poland; *Aleksandra Wójcicka,* Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology- Institute of Microelectronics and Optoelectronics, Poland; *Aneta Gołębiowska,* Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Poland; *Jarosław Tarenko, Oskar Sadowski, Maciej Kamiński,* Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology - Institute of Microelectronics and Optoelectronics, Poland; *Marcin Guza, Marek Wzorek,* Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Poland; *Justyna Wierzbicka,* Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Warsaw University of Technology - Institute of Microelectronics and Optoelectronics, Poland; *Krzysztof Czuba, Anna Szerling, Andrzej Taube,* Łukasiewicz Research Network-Institute of Microelectronics and Photonics, Poland

IWGO-MoP-25 Engineering Considerations for the Growth of Sb-Doped Sn0.4Ge0.6O2 Thin Films, ***Avery-Ryan Ansbro (Student)***, *Yi Liang, Pat Kezer, Manasi Londhe, John Heron,* University of Michigan, Ann Arbor

IWGO-MoP-28

Lock-in Infrared Thermography Techniques for Thermal Characterization of Ultra-Wide Bandgap Semiconductors, ***Ethan Scott***, *Jessica Reyes,* University of Virginia; *Jeffrey Braun, John Gaskins,* Laser Thermal; *Marko Tadjer,* Navel Research Laboratory; *Patrick Hopkins,* University of Virginia

IWGO-MoP-29

Reverse Leakage Reduction of β-Ga_2O_3 Schottky Barrier Diode by *Ex-Situ* Mg Annealing Diffusion, ***Zhiyu Xu***, *Jia Wang, Haitao Wang, Hiroshi Amano,* Nagoya University, Japan

IWGO-MoP-30

In-situ Reflectometry for Monitoring Growth Rate, Surface Morphology, and Doping in MOVPE Homoepitaxy of β-Ga_2O_3, ***Kolja Haberland***, LayTec AG, Germany; *Ta-Shun Chou,* NextGO Epi UG, Germany; *Andreas Fiedler, Adreas Popp, Saud Bin Anooz, Raimund Grüneberg, Jana Rehm, Arub Akhtar,* Institut für Kristallzüchtung IKZ, Germany

IWGO-MoP-31

Epitaxial β–$(Al_xGa_{1-x})_2O_3$ Thin Films Grown on (100) β-Ga_2O_3 by MOVPE, ***Deborah Kern (Student)***, *Martin Handwerg, Ta-Shun Chou, Saud Bin Anooz, Martin Schmidbauer, Andreas Popp, Andreas Fiedler,* Leibniz Institute for Crystal Growth, Germany

IWGO-MoP-32

NiO/β-Ga_2O_3 Vertical Pin Diodes with Low Leakage and Size Dependent Transport Characteristics, ***Tom Micottis (Student)***, Institute of Electronics, Microelectronics and Nanotechnology (IEMN), France

IWGO-MoP-33
Electronic and Electrical Properties of $Mg_xNi_{1-x}O$ Thin Films Deposited by Rf Magnetron Sputtering, ***Harunobu Yasuda (Student)***, *Shunya Matsui, Takayuki Akiba, Tomohiro Yamaguchi, Tohru Honda,* Department of Electrical Engineering and Electronics, Graduate School of Engineering, Kogakuin University, Japan*; Hironobu Miyamoto, Kohei Sasaki,* Novel Crystal Technology, Japan*; Takeyoshi Onuma,* Department of Electrical Engineering and Electronics, Graduate School of Engineering, Kogakuin University, Japan

IWGO-MoP-34
Improved Structural and Electrical Properties of MOCVD-Grown β-Ga_2O_3/Sapphire Films with Compositionally-Graded $(Al_xGa_{1-x})_2O_3$ Buffer, ***Filip Gucmann***, *Sai Gurukrishna Vadlamudi, Kristína Hušeková, Edmund Dobročka, Peter Nádaždy, Dagmar Gregušová, Iryna Kozak, Ondrej Pohorelec,* Institute of Electrical Engineering, Slovak Academy of Sciences, Slovakia*; Matej Mičušík,* Polymer Institute, Slovak Academy of Sciences, Slovakia*; Igor Píš, Milan Ťapajna,* Institute of Electrical Engineering, Slovak Academy of Sciences, Slovakia

IWGO-MoP-35
Reduction of Si Impurities in β-Ga_2O_3 Homoepitaxial Films Grown by Mist-CVD, ***Yuki Isobe (Student)***, Kyoto University, Japan*; Yuki Yamamoto,* OXIDE Corporation, Japan*; Hirokazu Izumi,* Hyogo Prefectural Institute of Technology, Japan*; Takeru Wakamatsu,* Kyoto University, Japan*; Kentaro Kaneko,* Ritsumeikan University, Japan*; Shizuo Fujita, Katsuhisa Tanaka,* Kyoto University, Japan

IWGO-MoP-36
Prospects of Safe and Cost-Effective Mist CVD for Homoepitaxial Growth and Devices of β-Ga_2O_3, ***Shizuo Fujita***, *Takeru Wakamatsu, Yuki Isobe, Hikaru Ikeda,* Kyoto University, Japan*; Yuji Ando, Hidemasa Takahashi, Ryutaro Makisako,* Nagoya University, Japan*; Tetsuzo Ueda,* Panasonic, Japan*; Jun Suda, Katsuhisa Tanaka,* Kyoto University, Japan*; Hidetaka Sugaya,* Panasonic, Japan

IWGO-MoP-39
First-Principles and Thermodynamic Study of (AlxGa1-x)2O3 Growth by PA-MBE, ***Rie Togashi***, Sophia University, Japan*; Akira Kusaba,* Kyushu University, Japan*; Masataka Higashiwaki,* Osaka Metropolitan University/NICT, Japan*; Yoshinao Kumagai,* Tokyo University of Agriculture and Technology, Japan

IWGO-MoP-40
Benchmarking Gate Charge in Gallium Oxide Transistors, ***Daniel Dryden***, Air Force Research Laboratory

IWGO-MoP-41
Defect Characterization of Czochralski Grown Gallium Oxide, *Alecsander Imhof,* ***Nadeemullah Mahadik***, Naval Research Laboratory*; Marko Tadjer,* Naval Research Laboratory*; Robert Lavelle,* Pennsylvania State University

IWGO-MoP-43
Gd Incorporation in β-Ga_2O_3 Grown by Suboxide MBE: Towards Ultraviolet Emission and Luminescent Thermometry, *Martin Samuel Williams, Marco Schowalter,* ***Alexander Karg***, *Mahmoud Elhajhasan,* University of Bremen, Germany*; Marcus Rohnke,* University of Giessen, Germany*; Carsten Ronning,* University of Jena, Germany*; Gordon Callsen, Andreas Rosenauer, Martin Eickhoff, Manuel Alonso-Orts,* University of Bremen, Germany

IWGO-MoP-46
Growth of NiO/ β-Ga_2O_3 Heterojunction Diodes using Plasma-Assisted Molecular Beam Epitaxy, ***Dagny Sacksteder (Student)***, Colorado School of Mines*; Anna Sacchi,* National Laboratory of the Rockies*; Megan Holtz,* Colorado School of Mines*; M. Brooks Tellekamp,* National Laboratory of the Rockies

IWGO-MoP-47 Domestic Supply-Chain Development of Discrete Ga2O3 Devices for Next-Generation Power Conversion Systems, ***Jesse Johnson***, Mainstream Engineering Corporation*; Luke Lyle, Robert Lavelle, Greg Pastir,* The Applied Research Laboratory at Penn State University*; Andrew Binder, Richard Floyd, Mihai Negoita, Brian Rummel, Bob Kaplar,* Sandia National Laboratories*; David Snyder, Justin Hill,* Mainstream Engineering Corporation

IWGO-MoP-48 Heteroepitaxial β-Ga_2O_3-on-SiC (GOSiC): Vertical Schottky Devices and Device-Predictive Cathodoluminescence, ***Dominic Lane***, Silanna

Room ESJ 0202

8:00am	**BREAKFAST**	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-TuM1** **Substrate Development and Material Quality I** **Moderators:** **Masataka Higashiwaki**, Osaka Metropolitan University/NICT, Japan, **Yoshinao Kumagai**, Tokyo University of Agriculture and Technology, Japan
8:30am	**INVITED: IWGO-TuM1-7** MOCVD Ga_2O_3: Interface and Phase Engineering, ***Xiuling Li,*** University of Texas Austin	
8:55am	**INVITED: IWGO-TuM1-12** Cost Analysis of Gallium Oxide Wafer Production and Challenges and Strategies for Cost Reduction, ***Akito Kuramata,*** *Takuya Igarashi, Shinya Watanabe,* Novel Crystal Technology, Inc., Japan*; Chia-Hung Lin,* Novel Crystal Technology, Inc., Taiwan*; Kohei Sasaki, Kimiyoshi Koshi,* Novel Crystal Technology, Inc., Japan	
9:20am	**INVITED: IWGO-TuM1-17** Dawn of a 7 eV Semiconductor: Si-doped α–$(Al_xGa_{1-x})_2O_3$, ***Darrell Schlom,*** Cornell University	
9:45am	**IWGO-TuM1-22** Demonstration of 150 mm (001) β-Ga2O3 Substrates Grown by EFG Method, ***Sho Hasegawa,*** *Kimiyoshi Koshi, Yuki Ueda, Ryoichi Sakaguchi,* Novel Crystal Technology, Inc., Japan*; Isao Sakamoto,* Novel Crystal Technology, Inc, Japan*; Keita Konishi, Makoto Mizui, Yu Yamaoka, Shinya Watanabe, Kohei Sasaki, Akito Kuramata,* Novel Crystal Technology, Inc., Japan	
10:00am	**IWGO-TuM1-25** Bulk Single Crystal Growth ofβ-Ga_2O_3 with Automatic Diameter Control System Specialized for the OCCC Method, ***Masanori Kitahara (Student),*** *Taketoshi Tomida,* FOX Corporation, Japan*; Vladimir Kochurikhin, Gushchina Liudmila,* C&A Corp, Russian Federation*; Yasuhiro Shoji, Kei Kamada,* FOX Corporation, Japan*; Koichi Kakimoto,* Tohoku University, Japan*; Akira Yoshikawa,* FOX Corporation, Japan	
10:15am	**IWGO-TuM1-28** Development of High-Quality 4” β-Ga_2O_3 (010) Wafer via the VB Method, ***Yuki Yamamoto,*** *Shigenori Shimizu,* OXIDE, Japan*; Kensuke Mizukoshi, Takashi Nishinoiri,* Ceratec Japan Co., Ltd., Japan*; Toshinori Taishi, Keigo Hoshikawa,* Shinshu Univ., Japan	
10:30am	**BREAK & EXHIBITS**	
11:00am	**INVITED: IWGO-TuM2-37** Defect Complexes and β-to-γ Phase Boundaries in Si-implanted Ga_2O_3, ***Naomi Pieczulewski (Student),*** *Katie Gann,* Cornell University*; Thaddeus Asel, Brenton Noesges,* Air Force Research Laboratory, Materials and Manufacturing Directorate, USA*; Michael Thompson, David Muller,* Cornell University	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-TuM2** **Substrate Development and Material Quality II** **Moderators:** **Zbigniew Galazka**, Leibniz Institute for Crystal Growth, Germany, **Kohei Sasaki**, Novel Crystal Growth, Japan
11:25am	**IWGO-TuM2-42** Thulium-doped Gallium Oxide Scintillators: Growth and Characterization, ***Marko Tadjer,*** *Lee Mitchell,* Naval Research Laboratory*; Robert Lavelle,* Pennsylvania State University Applied Research Laboratory*; Alex Lebedinsky,* University of Houston*; Darshana Wickramaratne, Evan Glaser,* Naval Research Laboratory*; Katie Gann, Tia Gray,* National Research Council*; Alan Jacobs, James Spencer Lundh, Steven Bennett,* Naval Research Laboratory*; Matthew Krohn,* Pennsylvania State University Applied Research Laboratory*; Bernard Phlips,* Naval Research Laboratory*; Kumar Saurabh, P. Shiv Halasyamani,* University of Houston*; Karl Hobart,* Naval Research Laboratory	
11:40am	**IWGO-TuM2-45** Growth of β-Ga_2O_3 Crystals by Plling-Down EFG Method with a Raw Material Supply System, ***Yuki Ueda,*** Novel Crystal Technology Inc., Japan*; Kimiyoshi Koshi, Sho Hasegawa, Kohei Sasaki, Akito Kuramata,* Novel Crystal Technology, Inc., Japan	
11:55am	**IWGO-TuM2-48** Redefining β-Ga_2O_3 Smart Cut™ Through Optimized Ion Implantation, ***Adrien Roth (Student),*** *Guillaume Gelineau, Lucas Colonel, Frédéric Mazen, Frédéric Milési, Florence Madeira, Nicolas Troutot,* CEA-Leti, France*; David Eon,* CNRS, France*; Julie Widiez,* CEA-Leti, France	
12:10pm	**IWGO-TuM2-51** HCl-based Halide Vapor Phase Epitaxy and HCl Gas Etching on (−112) β-Ga_2O_3 Substrates, ***Takayoshi Oshima,*** *Yuichi Oshima,* NIMS, Japan	

Tuesday Afternoon, August 4, 2026

	Room ESJ 0202	
2:00pm	**INVITED: IWGO-TuA1-1** Heterogeneous Gallium Oxide Integration and Vertical Device Technology, ***Martin Kuball,*** University of Bristol, UK	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-TuA1** **Heterogeneous Integration and other WBG and UWBG Oxides Beyond Ga_2O_3** **Moderators:** **Nolan Hendricks**, AFRL, **Man Hoi Wong**, The Hong Kong University of Science and Technology, Hong Kong
2:25pm	**IWGO-TuA1-6** >10 kV Vertical NiO_x/(011) β-Ga_2O_3 HJDs with PFOM >2.3 GW/cm2, ***Yizheng Liu (Student),*** *Carl Peterson, Chinmoy Saha,* University of California at Santa Barbara*; Marko Tadjer,* Naval Research Laboratory*; Sriram Krishnamoorthy,* University of California at Santa Barbara	
2:40pm	**IWGO-TuA1-9** Semiconductor Properties of Epitaxial NiGa2O4 Spinel That Forms at Ga_2O_3/NiO Interfaces, *Kingsley Egbo, Anna Sacchi, M. Brooks Tellekamp,* ***Andriy Zakutayev,*** National Laboratory of the Rockies	
2:55pm	**IWGO-TuA1-12** Breaking the 6 eV Barrier: Colossal Bandgap Electronics with Si Doped α-$(Al_xGa_{1-x})_2O_3$ by S-MBE, ***Debaditya Bhattacharya (Student),*** *Jacob Steele, Kazuki Nomoto, Naomi Pieczulewski,* Cornell University*; Preston Sorensen,* University of Nebraska - Lincoln*; Madhav Ramesh,* Cornell University*; Indika Senevirathna,,* Clark Atlanta University*; Mathias Schubert,* University of Nebraska - Lincoln*; David Muller, Huili Grace Xing, Darrell Schlom, Debdeep Jena,* Cornell University	
3:10pm	**IWGO-TuA1-15** Thin-Film β-Ga2O3 Composite Substrates for Thermal Management Solutions, ***Michael Liao,*** APEX Microdevices*; Mark Goorsky,* University of California Los Angeles*; Piyush Shah,* APEX Microdevices	
3:25pm	**BREAK & EXHIBITS**	
3:55pm	**IWGO-TuA2-24** Conductive Al_2O_3 with Ohmic Contacts via Ion Implantation, ***Alan Jacobs,*** *Katie Gann, James Lundh, Daniel Pennachio, Darshana Wickramaratne, Karl Hobart, Michael Mastro,* Naval Research Laboratory	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-TuA2** **Defects Science III & Thermal Management** **Moderators:** **Martin Kuball**, University of Bristol, UK, **Heather Splawn**, KYMA TECHNOLOGIES, INC.
4:10pm	**IWGO-TuA2-27** In-Situ X-Ray Topography Observation of Behavior of Dislocations in β-Ga_2O_3(001) Schottky Barrier Diode During Applying Voltage, ***Daiki Katsube,*** Japan Fine Ceramics Center, Japan*; Yongzhao Yao,* Mie University, Japan*; Daiki Wakimoto, Hironobu Miyamoto, Kohei Sasaki, Akito Kuramata,* Novel Crystal Technology, Japan*; Yukari Ishikawa,* Japan Fine Ceramics Center, Japan	
4:25pm	**IWGO-TuA2-30** Killer Defects in (011) HVPE-Grown β-Ga2O3 Schottky Barrier Diodes Studied by Synchrotron X-ray Topography and Emission Microscopy, ***Masanori Eguchi,*** Synchrotron Light Application Center, Saga University, Japan*; Shotaro Nakaniwa, Makoto Sato, Niloy Chandra Saha,* Department of Electrical and Electronic Engineering, Saga University, Japan*; Chia-Hung Lin, Kohei Sasaki,* Novel Crystal Technology, Japan*; Makoto Kasu,* Department of Electrical and Electronic Engineering, Saga University, Japan	
4:40pm	**IWGO-TuA2-33** Impact of Bias Dependent Joule Heating on Gallium Oxide Lateral Transistors via Deep UV Thermal Imaging, ***Dominic Myren (Student),*** University of Connecticut*; Daniel Dryden,* Air Force Research Laboratory*; Cameron Gorsak, Hari Nair,* Cornell University*; Ahmad Islam, Andrew Green,* Air Force Research Laboratory*; Georges Pavlidis,* University of Connecticut	
4:55pm	**IWGO-TuA2-36** Engineered Substrates for Ga_2O_3 Vertical Power Devices, ***Caroline Reilly,*** Kyma Technologies, Inc.*; Sean O'Leary,* Modern Microsystems, Inc.*; Emma Rocco,* US Naval Research Laboratory*; Craig McGray,* Modern Microsystems, Inc.*; Marko Tadjer, Karl Hobart,* US Naval Research Laboratory*; Heather Splawn, Jacob Leach,* Kyma Technologies, Inc.	
5:10pm		

International Workshop on Gallium Oxide and Related Materials (IWGO-6)

Room ESJ Concourse - Session IWGO-TuP

IWGO Poster Session II

Moderators:

A F M Anhar Uddin Bhuiyan, University of Massachusetts Lowell,

5:30 – 7:30 pm

IWGO-TuP-2

Cathodoluminescence Study of Rutile GeO_2 Grown via Mist CVD, ***Kazuki Shimazoe,*** *Shota Ishiyama,* Nagoya Institute of Technology, Japan*; Kazutaka Kanegae, Hiroyuki Nishinaka,* Kyoto Institute of Technology, Japan*; Masashi Kato,* Nagoya Institute of Technology, Japan

IWGO-TuP-4

Influence of Sapphire Substrate Orientation on Epitaxial Rutile GeO2 Thin Film Solar-Blind Photodetector Properties, ***Eriks Dipans (Student),*** *Edvards Strods, Sven Oras, Annamarija Trausa, Jevgenijs Gabrusenoks, Edgars Butanovs,* Institute of Solid State Physics, University of Latvia

IWGO-TuP-5

Effect of Unintentional Si Impurities on F-doped β-Ga_2O_3 Thin Films Grown by Mist CVD, ***Ichiro Seike (Student),*** Kyoto Institute of Technology, Japan*; Hiroki Miyake,* MIRISE Technologies Corporation, Japan*; Hiroyuki Nishinaka,* Kyoto Institute of Technology, Japan

IWGO-TuP-6

First Demonstration of p-type LiGa5O8 UWBG Thin Films by MOCVD, ***Dong Su Yu (Student),*** *Mingxuan Wu, Binzhi Liu, Md Mosarof Hossain Sarkar, Kaitian Zhang, Jinwoo Hwang, Hongping Zhao,* The Ohio State University

IWGO-TuP-7

Fabrication and Characteristics of α-Ga_2O_3-Based Schottky Barrier Diodes on Sapphire Substrates for Microwave Rectenna Applications, *Takeru Wakamatsu,* Kyoto University, Japan*; Yasuo Ohno,* Laser Systems Inc., Japan*; Hikaru Ikeda,* ***Shizuo Fujita,*** Kyoto University, Japan*; Tomomi Hiraoka,* Laser Systems Inc., Japan*; Kentaro Kaneko,* Ritsumeikan University, Japan*; Katsuhisa Tanaka,* Kyoto University, Japan

IWGO-TuP-8

Gigantic Space Charge Limited Currents and Thermal Effects in Si-Fe-doped Ga_2O_3 Devices, ***Pierre Gallarday (Student),*** *Aniol Vellvehí,* INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain*; Verena Leitgeb,* Department Microelectronics, Materials Center Leoben Forschung GmbH (MCL), Austria*; Miquel Vellvehí, Josep Montserrat,* INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain*; Barbara Kosednar-Legenstein, Lisa Mitterhuber, Elke Kraker, Anton Köck,* Department Microelectronics, Materials Center Leoben Forschung GmbH (MCL), Austria*; José Rebollo, Amador Pérez-Tomás,* INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain

IWGO-TuP-9

Conductive Si-doped β-Ga_2O_3 by Atomic Layer Deposition and Annealing, ***Katie Gann,*** *Benjamin Greenberg, Daniel Pennachio,* Naval Research Laboratory*; Jeffrey Woodward,* Naval research Laboratory*; Alan Jacobs, Emma Rocco, Boris Feygelson, Rachael Myers-Ward, Karl Hobart, Michael Mastro,* Naval Research Laboratory

IWGO-TuP-10

Atomic Scale Investigation of (100) Twin Boundary in EFG-Grown Sn-Doped β-Ga_2O_3, ***Mehidi Hassan (Student),*** *Binzhi Liu, Jinwoo Hwang,* Ohio State University

IWGO-TuP-11

Optimized CMP Processing and Subsurface Damage Control for High-Quality (010) β-Ga_2O_3 Single Crystals, *Won-Jae Lee,* ***Eun-Jeong An (Student),*** *Eun-Seo Lee, Sang-Jin Bae, Ho-Gyun Yun, Kwang-Hee Jung, Jung-Gon Kim, Mi-Seon Park,* Dong-eui university, Busan, Republic of Korea*; Jin-Ki Kang, Dong-Jin Lee,* Axel, Republic of Korea

IWGO-TuP-12

Heat-resistant Characteristics of Li doped NiO Films Deposited by RF Magnetron Sputtering, ***Shunya Matsui (Student),*** *Harunobu Yasuda, Tomohiro Ymaguchi, Tohru Honda,* Department of Electrical Engineering and Electronics, Kogakuin University, Japan*; Hironobu Miyamoto, Kohei Sasaki,* Novel Crystal Technology, Japan*; Takeyoshi Onuma,* Department of Electrical Engineering and Electronics, Kogakuin University, Japan

IWGO-TuP-14

Large-Area, UVC Passive Pixel Sensors based on Heteroepitaxial β-Ga_2O_3, *HyoJung Kim, SiSung Yoon,* ***GeonWook Yoo,*** Soongsil University, Republic of Korea

IWGO-TuP-15

Heteroepitaxial Growth of β-Ga2O3 on High-Angle Off-Cut Sapphire via MOCVD: Optimization through Minimum Oxygen Distance Simulations, ***Hyeong-Yun Kim (Student),*** *JungHun Choi, Ji-Hyeon Park, Dae-woo Jeon,* Korea Institute of Ceramic Engineering and Technology, Republic of Korea

IWGO-TuP-16

Defect- and Dopant-engineered p-type Conductivity in Epitaxial $ZnGa_2O_4$ Spinel Oxide Thin Films, *Mohammad M. Afandi, Yeongmin Park, Gyeong Ryul Lee,* ***Roy B. Chung,*** Kyungpook National University, Republic of Korea

IWGO-TuP-17

Remote Epitaxy of α-Ga_2O_3 via Polycrystalline MoS_2, *Gyeong Ryul Lee,* ***Yeongmin Park (Student),*** *Roy Chung,* Kyungpook National University, Republic of Korea

IWGO-TuP-18

β-Ga_2O_3 Growth on Single Crystal Diamond (111), *Arpit Nandi,* University of Bristol, UK*; Arnab Mondal, Ankush Bag,* Indian Institute of Technology Guwahati, India*;* ***Martin Kuball,*** University of Bristol, UK

IWGO-TuP-21

Epitaxial Growth of κ(ϵ)-Ga2O3 Thin Films on 4H-SiC Substrates by Mist Chemical Vapor Deposition, *Taisei Oya,* ***Kazuyuki Uno,*** Wakayama University, Japan

IWGO-TuP-22

Stability and Interlayer Formation at Epitaxial p-type Oxides/Ga_2O_3 Interfaces, ***Anna Sacchi,*** *Michelle Smeaton,* National Laboratory of the Rockies*; Shivashree Shivamade Gowda,* University of Virginia*; Krishna Acharya,* Colorado School of Mines*; Steven R. Spurgeon,* National Laboratory of the Rockies*; Patrick Hopkins,* University of Virginia*; Vladan Stevanovic,* Colorado School of Mines*; Brooks Tellekamp, Andriy Zakutayev,* National Laboratory of the Rockies

IWGO-TuP-23

Structural Properties of Sn-Doped β-Ga_2O_3 Thin Films Grown on Off-Axis Sapphire Substrates by Mist Chemical Vapor Deposition, ***Jae-Hyeok LIM (Student),*** *Yun-Ji SHIN, Tae-Yong Park, Seong-Min JEONG,* Korea Institute of Ceramic Engineering and Technology, Republic of Korea*; Chang-Mo KANG,* Pusan National University, Republic of Korea*; Si-Young BAE,* Pukyoung National University, Republic of Korea

IWGO-TuP-24

Enhanced Surface Engineering and Deep Mesa Etching in Vertical Ru-Si-O/β-Ga_2O_3 Schottky Diodes, ***Aleksandra Wojcicka (Student),*** Lukasiewicz Research Network - Institute of Microelectronics and Photonics, Poland

IWGO-TuP-27

Investigation of NiO/Ga_2O_3 Heterojunction PN Diodes by using HF Surface Treatment, ***Ray Hua Horng,*** National Yang Ming Chiao Tung University (NYCU), Taiwan

IWGO-TuP-28

Mechanism and Mitigation of Step-Bunching Instability in Homoepitaxial (100) β-Ga_2O_3 Thin Films, ***Ta-Shun Chou,*** *Saud Bin Anooz, Zbigniew Galazka, Jana Rehm, Arub Akhtar, Martin Albrecht, Andreas Fiedler, Andreas Popp,* Leibniz Institute for Crystal Growth, Germany

IWGO-TuP-29

α-Ga_2O_3 Thin Film Grown on Micropatterned Sapphire Substrate, ***Kotaro Etokoro (Student),*** Kyoto University, Japan*; Takeru Wakamatsu, Yuki Isobe,* kyoto University, Japan*; Kentaro Kaneko,* Ritsumeikan university, Japan*; Katsuhisa Tanaka,* Kyoto University, Japan

IWGO-TuP-30

Stabilization of Rutile GeO_2 on R- and M-Plane Al_2O_3 by Plasma-Assisted Molecular Beam Epitaxy, ***Alexander Karg,*** *Satjawoot Phiw-Ondee, Manuel Alonso-Orts, Martin Samuel Williams, Marco Schowalter, Andreas Rosenauer, Martin Eickhoff,* University of Bremen, Germany*; Patrick Vogt,* Paul-Drude-Institut für Festkörperelektronik Leibniz-Institut im Forschungsverbund Berlin, Germany

IWGO-TuP-31

Deep-Etch Mesa Edge Termination for β-Ga_2O_3 Schottky Barrier Diodes, ***Charlotte Conway (Student),*** *Aditya K Bhat, Sai Charan Vanjari,* University of Bristol, UK*; Jacob Mitchell, Jay Burnett, Kerry Roberts, Huma Ashraf,* KLA Corporation UK Ltd, UK*; Matthew Smith, Xiao Tang, Martin Kuball,* University of Bristol, UK

IWGO-TuP-32

Plasma-Assisted MBE of β-Ga_2O_3/NiO Heterojunctions, *Andy Séguret,* Université Grenoble-Alpes, CEA, Grenoble INP, IRIG, PHELIQS, France*; Marty Volant,* Université Grenoble-Alpes, CEA, IRIG, MEM, France*; Fabien Jourdan,* Université Grenoble-Alpes, CEA, Grenoble INP, IRIG, PHELIQS, France*; Yann Genuist,* Université Grenoble-Alpes, CNRS, Grenoble INP, Institut Néel, France*; Hervé Roussel,* Université Grenoble Alpes, CNRS, Grenoble INP, LMGP, France*; Hanako Okuno,* Université Grenoble-Alpes, CEA, IRIG, MEM, France*; Eirini sarigiannidou,* Université Grenoble Alpes, CNRS, Grenoble INP, LMGP, France*; Vincent Consonni,* 2. Université Grenoble Alpes, CNRS, Grenoble INP, LMGP, France*; Eva Monroy,* ***Julien Bosch,*** Université Grenoble-Alpes, CEA, Grenoble INP, IRIG, PHELIQS, France

IWGO-TuP-33
Long-Term Performance of Gallium Oxide-Based Hydrogen Sensors at 600˚C, ***William Callahan,*** National Laboratory of the Rockies; *Kingsley Egbo,* Headway Technologies; *Anna Sacchi, Davi Febba,* National Laboratory of the Rockies; *Anna Staerz, Ryan O'Hayre,* Colorado School of Mines; *Brooks Tellekamp, Andriy Zakutayev,* National Laboratory of the Rockies

IWGO-TuP-35
Band Alignment of NiO_X/β-Ga_2O_3(001) Heterojunction Consistently Determined by *I-V, C-V,* and IPE Measurements, ***Akihira Munakata (Student),*** University of Tokyo, Japan; *Hironobu Miyamoto, Kohei Sasaki,* Novel Crystal Technology, Inc., Japan; *Takuya Maeda,* University of Tokyo, Japan

IWGO-TuP-37
Deep-Acceptor-Mediated Inversion Enabling Normally-Off β-Ga_2O_3 MOSFETs without Epitaxy, *Sarit Dhar, Tamara Isaacs-Smith,* Auburn University; *Jacob Lawson, Charles Ebbing, Chase Kitzmiller,* ***J. Neil Merrett,*** Air Force Research Laboratory, USA

IWGO-TuP-40
Vertical Trench-Mos Barrier Diode on (001) β-Ga_2O_3 with Trench Formation by Hot H_3PO_4 Treatment, ***Aaron Adams,*** KBR/AFRL

IWGO-TuP-41
Challenges and Solutions in Mist-CVD of Ga_2O_3 Heteroepitaxial Films, ***Roman Yatskiv,*** Institute of Photonics and Electronics of the Czech Academy of Sciences, Czechia

IWGO-TuP-42
Plasma-Assisted Surface Pretreatment of Sapphire Substrates for High-Performance β-Ga_2O_3Solar-Blind Photodetectors, ***An-Na Cha,*** *Gieop Lee,* Chonnam National University, Republic of Korea; *Sunjae Kim,* University of Oslo, Norway; *Dae-Woo Jeon, Ji-Hyeon Park,* Korea Institute of Ceramic Engineering and Technology, Republic of Korea; *Wan-Sik Hwang,* Korea Aerospace University, Republic of Korea; *Jun-Seok Ha,* Chonnam National University, Republic of Korea

IWGO-TuP-43
Effect of Thermal Treatment on the Heteroepitaxial Growth of Ga2O3 on Sapphire Substrates, ***Gieop Lee (Student),*** *An-Na Cha, Sang Hyeon Ahn,* Chonnam National University, Republic of Korea; *Sung Jin Son, Young-Boo Moon, Myung Sik Kim,* UJL Inc., Republic of Korea; *Moo Sung Lee, Jun-Seok Ha,* Chonnam National University, Republic of Korea

IWGO-TuP-44
Area-Dependent Effects on the Breakdown Voltage of β-Ga_2O_3 Schottky Barrier Diodes for Scaling to High-Absolute Currents, ***Wolfgang Buchmaier (Student),*** Univeristy of California, Santa Barbara; *Steve Rebollo, Yizheng Liu, Sriram Krishnamoorthy, James Speck,* University of California at Santa Barbara

IWGO-TuP-45
Nitrogen-Doped Epitaxial Structures Towards Scalable Enhancement Mode Vertical Devices, ***Rachel Kahler (Student),*** *Carl Peterson, Yizheng Liu, Chinmoy Nath Saha, Steve Rebollo, Jim Speck, Sriram Krishnamoorthy,* University of California, Santa Barbara

IWGO-TuP-46 Identification of Facets Formed on (011) β-Ga_2O_3 Homoepitaxial Layers, ***Yuichi Oshima,*** *Takayoshi Oshima,* National Institute for Materials Science, Japan

IWGO-TuP-47 Self-Exfoliated α-Ga_2O_3 Flakes for Vertical Electronic and Optoelectronic Devices, ***Sunjae Kim,*** University of Oslo, Norway; *Wan Sik Hwang,* Korea Aerospace University, Republic of Korea; *Dae-woo Jeon,* Korea Institute of Ceramic Engineering and Technology, Republic of Korea; *Andrej Kuznetsov,* University of Oslo, Norway; *Ji-Hyeon Park,* Korea Institute of Ceramic Engineering and Technology, Republic of Korea

IWGO-TuP-48 Simulation of Amorphous Aluminum Gallium Oxide (Ago) Films for Memristor Devices, ***Joshua Stoner (Student),*** *Michael Mitchell, Shweta Joshi,* The George Washington University; *Olaf Vant 'T Erve,* Naval Research Laboratory; *Daniel Gopman,* NIST; *Gina Adam,* The George Washington University

Wednesday Morning, August 5, 2026

	Room ESJ 0202	
8:00am	**BREAKFAST**	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-WeM1** **Plenary Session II** **Moderators:** **Martin Albrecht**, Leibniz Institute for Crystal Growth, Germany, **Huili (Grace) Xing**, Cornell University
8:45am	**INVITED: IWGO-WeM1-10** PLENARY: From Crystal Growth to Power Devices: The Evolution of Gallium Oxide Technology, ***Kohei Sasaki,*** Novel Crystal Technology, Inc., Japan	
9:30am	**INVITED: IWGO-WeM1-19** Homoepitaxial Growth of β-Ga_2O_3 Using HVPE and MOVPE, ***Yoshinao Kumagai,*** Tokyo University of Agriculture and Technology, Japan	
9:55am	**INVITED: IWGO-WeM1-24** Characterization of Shallow and Deep Level Defects in β-(AlxGa1-x)2O3 Bulk Crystals, ***Andreas Fiedler,*** Leibniz-Institut für Kristallzüchtung, Germany	
10:20am	**BREAK & EXHIBITS**	
10:50am	**IWGO-WeM2-35** Structural and Electrical Properties of *c*-plane α-Ga_2O_3 Grown on High-quality α-Cr_2O_3 Templates by HVPE, ***Yuichi Oshima,*** *Takayoshi Oshima,* National Institute for Materials Science, Japan*; Shiyu Xiao, Kazuto Murakami, Katsuhiro Imai, Takahiro Tomita,* NGK INSULATORS, LTD, Japan	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-WeM2** **Epitaxial Growth and Doping Control II** **Moderators:** **Ahmad Islam**, AFRL, **Sriram Krishnamoorthy**, University of California Santa Barbara
11:05am	**IWGO-WeM2-38** Homoepitaxial Growth on (0-1-1) *β*-Ga_2O_3 Substrates Using Oxide Vapor Phase Epitaxy, ***Tomoka Nishikawa (Student),*** The University of Osaka, Japan*; Chia-Hung Lin, Kohei Sasaki, Akito Kuramata,* Novel Crystal Technology, Inc., Japan*; Eisho Kishimoto, Tomoyuki Tanikawa, Ryuji Katayama, Shigeyoshi Usami, Masayuki Imanishi, Yusuke Mori,* The University of Osaka, Japan	
11:20am	**IWGO-WeM2-41** Fe Compensation Doping and Interface Stability for Mitigating Interfacial Si Conductivity in MBE-Grown β-Ga_2O_3 Thin Films, ***Brenton Noesges,*** *Prescott Evans, Jian Li,* Core4ce*; Mark Gordon,* University of Dayton*; Daram Ramdin,* Core4ce*; Nicholas Sepelak,* KBR*; Daniel Dryden,* Air Force Research Lab, Sensors Directorate*; Shin Mou, Adam Neal, Thaddeus Asel,* Air Force Research Laboratory, Materials and Manufacturing Directorate	
11:35am	**IWGO-WeM2-44** Coherent Growth of α-(Al,Ga)2O3 on α-Cr2O3 Templates by Mist-CVD, ***Riena Jinno,*** The University of Tokyo, Japan*; Shiyu Xiao,* NGK Insulators, Ltd, Japan*; Takayoshi Oshima,* NIMS (National Institute for Materials Science), Japan*; Satoshi Iwamoto,* The University of Tokyo, Japan*; Kazuto Murakami,* NGK Insulators, Ltd., Japan*; Katsuhiro Imai, Takahiro Tomita,* NGK Insulators, Ltd, Japan	
11:50am	**IWGO-WeM2-47** Demonstration of Homojunction Ga2O3 PiN Diodes with High Bipolar Injection, ***Pierre Gallarday (Student),*** *Aniol Vellvehí, Miquel Vellvehí, José Rebollo, Josep Montserrat,* INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain*; Corine Sartel, Yves Dumont, Ekaterine Chikoizde,* Groupe d'étude de la matière condensée (GEMaC) - UVSQ, France*; Amador Pérez-Tomás,* INSTITUTE OF MICROELECTRONICS OF BARCELONA - (IMB-CNM-CSIC), Spain	
12:05pm	**IWGO-WeM2-50** Uniform Growth of Thick Homoepitaxial β-Ga_2O_3 Layers on 2-inch (010) Substrates by Low-Pressure Hot-Wall MOVPE, ***Yoshiki Iba (Student),*** *Yuma Terauchi,* Tokyo University of Agriculture and Technology, Japan*; Junya Yoshinaga,* TAIYO NIPPON SANSO CORPORATION, Japan*; Yasuhiro Hashimoto,* Sumitomo Metal Mining Co. Ltd., Japan*; Yoshinao Kumagai,* Tokyo University of Agriculture and Technology, Japan	

International Workshop on Gallium Oxide and Related Materials (IWGO-6)
Room ESJ 0202 - Session IWGO-WeA
Advanced Device Scaling and Fabrication Techniques I
Moderators: Siddarth Rajan, The Ohio State University,
Yuhao Zhang, University of Hong Kong

2:00pm	**INVITED: IWGO-WeA-1** Recent Advances in β–Ga_2O_3 Power and RF Device Technologies, ***Uttam Singisetti,*** University at Buffalo	
2:25pm	**IWGO-WeA-6** 1.5 kV/0.6 A Double Pulse Test Switching Of Cr_2O_3/β-Ga_2O_3 Heterojunction Diodes With > 3 kV Breakdown Voltages And Record Low Reverse Recovery Charge, ***Chinmoy Nath Saha,*** University of California Santa Barbara; *Yuzhou Yao, Juchen Yang,* The Ohio State University; *Yizheng Liu,* University of California at Santa Barbara; *Pengyu Fu, Shuwei He,* The Ohio State University; *James S. Speck,* University of California at Santa Barbara; *Jin Wang,* The Ohio State University; *Sriram Krishnamoorthy,* University of California at Santa Barbara	
2:40pm	**IWGO-WeA-9** Sub-Micron β-Ga2O3 FinFETs with >700 mA/mm Current Density and >10^8 ON/OFF Ratio Using Si δ-Doped Channels, ***Nabasindhu Das (Student),*** Arizona State University	
2:55pm	**IWGO-WeA-12** Over 3 kV Ultra-low Leakage Vertical (011) β-Ga_2O_3 Diodes with Schottky Contact Engineering and High-κ Field Plate, ***Emerson Hollar (Student),*** *Esmat Farzana,* Iowa State University	
3:10pm	**IWGO-WeA-15** Vertical Ga_2O_3(010) FinFETs Processed with Nitrogen Radical Irradiation, ***Zhenwei Wang,*** National Institute of Information and Communications Technology, Japan; *Jin Inajima, Kohki Tsujimoto, Yusuke Teramura,* Osaka Metropolitan University, Japan; *Yoshiki Iba, Yuma Terauchi,* Tokyo University of Agriculture and Technology, Japan; *Junya Yoshinaga,* Tokyo University of Agriculture and Technology/TAIYO NIPPON SANSO CORPORATION, Japan; *Takafumi Kamimura,* National Institute of Information and Communications Technology, Japan; *Yoshinao Kumagai,* Tokyo University of Agriculture and Technology, Japan; *Masataka Higashiwaki,* Osaka Metropolitan University/NICT, Japan	
3:25pm	**IWGO-WeA-18** Enhancement-Mode Ga_2O_3 CAVETs with Improved Breakdown Voltage by Hot Implantation, ***Jun Morihara (Student),*** Osaka Metropolitan University, Japan; *Daisuke Matsuo, Shun Konno, Kosuke Usui, Shinya Takemura,* Nissin Ion Equipment Co., Ltd., Japan; *Zhenwei Wang,* National Institute of Information and Communications Technology, Japan; *Romualdo Ferreyra,* Osaka Metropolitan University, Japan; *Kohei Tanaka,* Nissin Ion Equipment Co., Ltd., Japan; *Masataka Higashiwaki,* Osaka Metropolitan University, Japan	
3:40pm	**IWGO-WeA-21** Enhancement-Mode Vertical β-Ga_2O_3 U-Trench MOSFET with N-doped CBL and MOCVD regrown n^+ Contact Layers, ***Walid Amir,*** *Jiawei Liu, Surajit Chakraborty,* University at Buffalo-SUNY; *Dongsu Yu, Md. Mosarof Hossain Sarkar, Hingping Zhao,* Ohio State University; *Uttam Singisetti,* University at Buffalo-SUNY	

International Workshop on Gallium Oxide and Related Materials (IWGO-6)

Room ESJ Concourse - Session IWGO-WeP

IWGO Poster Session III

Moderators: Hari Nair, Cornell University,
Saurav Roy, North Carolina State University
4:00 – 6:00 pm

IWGO-WeP-2
Electrical Characterization of Mist-CVD HfO_x/β-Ga_2O_3 MIS Capacitor, ***Hayato Tanikawa (Student)***, kyoto Institute of Technology, Japan; *Kazutaka Kanegae, Hiroyuki Nishinaka,* Kyoto Institute of Technology, Japan

IWGO-WeP-3
Tuning the Conductivity of p-type $Ni_{1-x}O$ Thin Films for $Ni_{1-x}O/\beta$-Ga_2O_3 Heterojunction Power Devices, ***Thomas Ribault (Student)***, *Akash Patnaik, Bruno Berini, Corinne Sartel,* CNRS-UVSQ, France; *Yunlin Zheng, Jean-Louis Cantin,* CNRS-INSP, France; *Zurab Kushitashvili, Amiran Bibilashvili,* Institute of Nano et Microelectronics, Tbilisi, Georgia; *Tom Micottis, Farid Medjdoub,* CNRS-I.E.M.N., France; *Ekaterine Chikoidze, Yves Dumont,* CNRS-UVSQ, France

IWGO-WeP-4
Electro-Optical Metrology Development to Probe Deep-Level Traps in β-Ga2O3 MOSFETs, *Ory Maimon,* George Mason University; *Neil Moser,* Air Force Research Laboratory; *Pragya Shrestha, Min-Yeong Kim,* National Institute for Science and Technology (NIST); *Sang-Mo Koo,* Kwangwoon University, Republic of Korea; *Kyle Liddy, Andrew Green, Kelson Chabak,* Air Force Research Laboratory; *Qiliang Li,* George Mason University; ***Sujitra Pookpanratana***, National Institute for Science and Technology (NIST)

IWGO-WeP-6
Growth of 2-inch n-type β-Ga_2O_3 (011) Single Crystal by the VB Method, ***Yuki Ueda***, *Takuya Igarashi, Kimiyoshi Koshi, Sho Hasegawa, Ryoichi Sakaguchi, Taiki Chujo, Ryo Shinagawa, Kohei Sasaki, Akito Kuramata,* Novel Crystal Technology, Inc., Japan

IWGO-WeP-7
c-In_2O_3 Growth by Oxide Vapor Phase Epitaxy Using In_2O and H_2O Source Gases, ***Rie Togashi***, *Takumi Shimazaki,* Sophia University, Japan; *Masato Ishikawa,* Gas-Phase Growth Ltd., Japan

IWGO-WeP-9
Characterization of p-Cr_2O_3/n-Ga_2O_3 Heterojunction Rectifiers, *Hannah Masten, Frank Kelly,* National Research Council; *Chinmoy Nath Saha, Yizheng Liu,* University of California at Santa Barbara; *Tia Gray,* National Research Council; *Sriram Krishnamoorthy,* University of California at Santa Barbara; *Marko Tadjer,* ***Karl Hobart***, Naval Research Laboratory

IWGO-WeP-10
Temperature Dependent Hall as a Probe for Parasitic Conduction in Gallium Oxide Epitaxial Structures, ***Joshua Buontempo (Student)***, *Cameron Gorsak, Pushpanshu Tripathi, Hari Nair,* Cornell University

IWGO-WeP-11
3D Modeling of EFG β-Ga_2O_3 Crystal Growth: Effect of Process on Crystal Quality, ***Alex Galyukov***, STR US, Inc.; *Aleksa Crnobrnja, Andrey Smirnov,* STR Europe, Serbia

IWGO-WeP-12
Multi-Ribbon Growth of Offcut (100) β-Ga_2O_3 by EFG, ***Kurt Lindquist***, *David Joyce, Kale Geddis, Drew Haven,* Luxium Solutions, LLC; *Robert Lavelle, Luke Lyle, Benjamin Dutton,* Penn State University

IWGO-WeP-14
Composition-Dependent Thermal Conductivity of $Ge_xSn_{1-x}O_2$ Alloys, ***Xiao Zhang***, *Emmanouil Kioupakis,* University of Michigan, Ann Arbor

IWGO-WeP-15
MOCVD Growth and Characterization of β-Ga_2O_3 Field Effect Transistors Grown on 2” (010) Substrates, ***Will Brand***, *Fikadu Alema,* Agnitron Technology; *Austin Hickman,* Soctera; *Andrei Osinsky,* Agnitron Technology

IWGO-WeP-16
DRCLS Defects Near $LiGa_5O_8/Ga_2O_3$ Heterointerfaces, ***Carlos DeLeon (Student)***, *Kaitian Zhang, Hongping Zhao, Leonard Brillson,* Ohio State University

IWGO-WeP-17
Electric-Field-Limited Breakdown in Oxide/β-Ga2O3 p–n Heterojunction Diodes, ***Sanjay Gopalan***, *John Muth, Ki Wook Kim,* North Carolina State University

IWGO-WeP-18
Hot-wall MOCVD Growth on Miscut (100) β-Ga2O3 Substrates, ***Benjamin Dutton***, *Robert Lavelle, Luke Lyle, Randal Cavalero, Connor Beakes, Scott Pistner,* Penn State University Applied Research Laboratory; *Drew Haven, David Joyce,* Luxium Solutions LLC; *David Snyder,* Penn State University Applied Research Laboratory

IWGO-WeP-19
Temperature-Optimized Lattice-Matched Epitaxy of UWBG Rutile $Ge_xSn_{1-x}O_2$ on (001) Rutile TiO_2, ***Satyam Patel (Student)***, *Becky (R.L.) Peterson,* University of Michigan, Ann Arbor

IWGO-WeP-20
Growth of Rutile-Type GeO_2 by Oxide Vapor Phase Epitaxy, ***Haru Nakano (Student)***, *Shigeyoshi Usami, Masayuki Imanishi, Yusuke Mori,* Osaka University, Japan

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Thermodynamic analysis of GeO_2 growth via Oxide Vapor Phase Epitaxy, ***Shigeyoshi Usami***, *Masayuki Imanishi, Yusuke Mori,* The University of Osaka, Japan

IWGO-WeP-22
Experimental Study of Hf-Doped β-Ga_2O_3 by Floating Zone Method, ***Myeonggyun Kang (Student)***, Tohoku University, Japan, Republic of Korea; *Kei Kamada, Hisato Suezumi, Masanori Kitahara, Satoshi Ishizawa, Rikito Murakami, Yuui Yokota, Masao Yoshino, Akira Yoshikawa,* Tohoku University, Japan

IWGO-WeP-24
Re-Growth on Multi-Directional Fin Structures of (001) β-Ga_2O_3, ***Sai Kkrishna Anandan (Student)***, *Min-Yeong Kim, Arpit Nandi, Martin Kuball,* University of Bristol, UK

IWGO-WeP-25
Surface Termination and Structural Stability of β-(AlXGa1−X)2O3 (100) (X = 0 ~ 0.3) as-Cleaved Single Crystals, ***Ming-Chao Kao (Student)***, Deutsches Elektronen-Synchrotron DESY (NanoLab), Germany

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Effect of the GaN Surface on n-Ga_2O_3/p-GaN Heterointerface Quality, ***Daniel Pennachio***, US Naval Research Laboratory; *Frank Kelly, Katie Gann,* National Research Council Postdoctoral Fellow, residing at NRL; *Emma Rocco, Michael Mastro,* US Naval Research Laboratory

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p-GaN/n-Ga_2O_3 Diodes via MOCVD Selective Area Growth, ***Frank Kelly***, *Emma Rocco, Daniel Pennachio, James Lundh, Alan Jacobs, Tolen Nelson, Marko Tadjer, Michael Mastro,* Naval Research Laboratory

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Performance of MOCVD Grown Schottky Barrier Diodes with a Graded β-$(Al,Ga)_2O_3$ Cap, ***Cameron Gorsak***, *Frank Kelly, Jenifer Hajzus, Daniel Pennachio,* Naval Research Laboratory; *Katie Gann,* Naval Research Laboratory, USA; *Alan Jacobs, Emma Rocco, Michael Mastro,* Naval Research Laboratory

IWGO-WeP-29
Vertical β-Ga_2O_3 U-Trench MOSFETs With N-ion-implanted Current Blocking Layer and Implanted Source, ***Jiawei Liu (Student)***, *Surajit Chakraborty, Walid Amir, Uttam Singisetti,* University at Buffalo-SUNY

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Donor Doping of β-Ga_2O_3 by Cl Ion Implantation, ***Katie Gann***, *Alan Jacobs, Frank Kelly, Emma Rocco, Cameron Gorsak, Marko Tadjer,* Naval Research Laboratory; *Rachael Myers-Ward,* naval research Laboratory; *Karl Hobart, Michael Mastro,* Naval Research Laboratory

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Thermodynamic analysis of (AlxGa1-x)$2O_3$ MOCVD growth with TMA, O_2, and TMG and TEG as Ga precursors, ***Andri Dhora (Student)***, Lund University, Sweden

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Effect of Ga Etching and Wet Acid Treatments on MOS Characteristics for Vertical β-Ga2O3 Power Devices, ***Akhila Mattapalli (Student)***, *Chinmoy Nath Saha,* University of California at Santa Barbara; *Carl Peterson, Steve Rebollo, Jim Speck, Sriram Krishnamoorthy,* University of California Santa Barbara

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High-Temperature Stability of Contacts to β-Ga_2O_3, ***Donivan R. Mouck (Student)***, The Applied Research Lab at The Pennsylvania State University; *Paul Kelemen, Sohyun Lee, Nathan S. Banner, Chan-Wen Chiu, Suzanne E. Mohney,* Pennsylvania State University; *Luke A. M. Lyle,* The Applied Research Lab at The Pennsylvania State University

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Group-III Flux Etching of β-(AlxGa1-x)2O3 Heterostructures, ***Emma Rocco***, *Frank Kelly, J. S. Lundh, Daniel Pennachio, Katie Gann, Cameron Gorsak, Alan Jacobs, Marko Tadjer, Michael Mastro,* U.S. Naval Research Laboratory

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High-Reflectance In-Plane Ga_2O_3/Air DBRs Fabricated by HEATE on (010) β-Ga_2O_3, ***SOTARO IIJIMA (Student)***, *TAKAHASHI YUKI,* Sophia Univ, Japan*; AKIHIKO KIKUCHI,* Sophia Univ / Sophia Semiconductor Research Institute, Japan

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Phase-Dependent Photoluminescence of Near-Infrared Color Centers in Ga_2O_3, ***Keidai Toyoshima (Student)***, The University of Tokyo, Japan*; Mathias Marchal,* Technical University of Denmark, Denmark*; Riena Jinno, Satoshi Iwamoto,* The University of Tokyo, Japan

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Transmutation-doped β-Ga2O3 via Thermal Neutron Irradiation, ***Richard Barber (Student)***, University of Missouri*; Marko Tadjer, Evan Glaser,* Naval Research Laboratory*; Marc Weber,* Washington State University*; Alison Hartman,* University of Missouri-Columbia*; Jaime Freitas, Steven Bennett, Mason Klemm, Alan Jacobs, Karl Hobart,* Naval Research Laboratory*; Kohei Sasaki, Akito Kuramata,* Novel Crystal Technology, Japan*; P. Shiv Halasyamani,* University of Houston*; Blaine Reid, John Brockman, John Gahl,* University of Missouri

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Optimizing β-Ga_2O_3 MOCVD Regrowth for Vertically Scaled Channels, ***Julian Gervassi-Saga (Student)***, *Nabasindhu Das, Advait Gilankar, Nidhin Kurian Kalarickal,* School of Electrical, Computer and Energy Engineering, Arizona State University

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962 V Ga_2O_3 Schottky Power Diodes on (011) Substrate, ***Luoyuan Jiang (Student)***, *Md Mosarof Hossain Sarkar, Yibo Xu, Hongping Zhao, Wu Lu,* Ohio State University

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Identifying the Origin of Emissions and Anisotropic Properties of Different Crystallographic Orientation Sn-Doped β-Ga_2O_3 Substrates, ***Kishor Upadhyaya***, King Abdullah University of Science and Technology, India*; Andres Hurtado,* King Abdullah University of Science and Technology, Colombia*; Hadeel Alamoudi, Iman Roqan,* King Abdullah University of Science and Technology, Saudi Arabia

IWGO-WeP-43

First-Principles Insight into Boron-Vacancy Clusters as Shallow Acceptors in Diamond for p-Type UWBG Applications, ***Md Abdullah Al Mamun (Student)***, *Jongchan Kim,* The University of Texas at Dallas*; Katherine T. Fountaine, Vincent Gambin,* Northrop Grumman*; Kyeongjae Cho,* The University of Texas at Dallas

IWGO-WeP-45

Study of Si-Implanted AlN by High Temperature Annealing, ***Yinan Zhao (Student)***, *Pantao Hu, Hsin-Wei (Sheena) Huang, Debdeep Jena, Robert Bruce van Dover, Michael Olgar Thompson,* Cornell University

Wednesday Evening, August 5, 2026

International Workshop on Gallium Oxide and Related Materials (IWGO-6)
Room ESJ 0202 - Session IWGO-WeE
IWGO Rump Session
Moderator: Ali Sayir, Air Force Office of Scientific Research

6:00pm

PANELISTS:

- **John Frank,** Luxium Solutions
- **Katie Gann,** US Naval Research Laboratory
- **Andrew Green,** AFRL
- **Masataka Higashiwaki**, Osaka Metropolitan University/National Institute of Information and Communications Technology
- **Fritz Kub,** US Naval Research Laboratory
- **Akito Kuramata,** Novel Crystal Technology
- **Jon McCandless**, Gallox Semiconductors
- **Victor Veliadis**, Power America; NC State
- **Man-Hoi Wong**, Hong Kong University of Science and Technology

Thursday Morning, August 6, 2026

	Room ESJ 0202	
8:00am	**BREAKFAST**	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-ThM1** **Theory, Modeling, and Simulation** **Moderators:** **Jinwoo Hwang**, The Ohio State University, **Joel Varley**, Lawrence Livermore National Laboratory
8:30am	**INVITED: IWGO-ThM1-7** Impact of Defects and Impurities on the Properties of Al2O3, ***Chris G. van de Walle,*** UCSB	
8:55am	**INVITED: IWGO-ThM1-12** GeO_2 and $Ge_xSn_{n1-x}O_2$ Alloys: Emerging Ultra-Wide-Band-Gap Materials for Power Electronics, ***Emmanouil (Manos) Kioupakis,*** University of Michigan, Ann Arbor	
9:20am	**IWGO-ThM1-17** Rutile $Ge_xSn_{1-x}O_2$ Alloys for Ultra-Wide Bandgap Electronics: Phase Stability and Bandgap Engineering, ***Alp Kurbay (Student),*** University of Michigan, Ann Arbor; *Yann Müller,* EPFL, Switzerland; *Xiao Zhang,* University of Michigan, Ann Arbor; *Anirudh Natarajan,* EPFL, Switzerland; *Emmanouil Kioupakis,* University of Michigan, Ann Arbor	
9:35am	**IWGO-ThM1-20** Single Ga-Layer Reconstruction Mediates Ga_2O_3 Heteroepitaxy: A Multiscale Atomistic Study, ***Ilaria Bertoni (Student),*** *Aldo Ugolotti, Anna Marzegalli,* Universita' degli Studi di Milano-Bicocca, Italy; *Flyura Djurabekova,* University of Helsinki, Finland; *Leonida Miglio,* Universita' degli Studi di Milano-Bicocca, Italy	
9:50am	**IWGO-ThM1-23** Carrier Mobility in $Ge_xSn_{1-x}O_2$ Alloys from First Principles, ***Amanda Wang (Student),*** *Alp Kurbay, Xiao Zhang, Nick Pant, Emmanouil Kioupakis,* University of Michigan	
10:05am	**IWGO-ThM1-26** A Novel Vertical β-Ga2O3 Transistor Architecture Without Planarization or Mid-Gap Acceptor Blocking Layers, ***Akilesh Srikanth (Student),*** The Ohio State University; *Siddharth Rajan,* Ohio State University	
10:20am	**BREAK & EXHIBITS**	
10:50am	**INVITED: IWGO-ThM2-35** 4D-STEM and Machine Leaning Investigation of Defects and Polymorphism in Ultra Wide Band Gap Oxides and Nitrides, ***Jinwoo Hwang,*** The Ohio State University	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-ThM2** **Defects Science IV** **Moderators:** **Emma Rocco**, Naval Research Laboratory, **Chris G. van de Walle**, University of California Santa Barbara
11:15am	**IWGO-ThM2-40** Bandgap Renormalization in Si-doped β-Ga_2O_3 Films, ***Takeyoshi Onuma,*** *Kai Yamamoto, Kyohei Tanaka,* Kogakuin University, Japan; *Yoshiki Iba,* Tokyo University of Agriculture and Technology, Japan; *Junya Yoshinaga,* TAIYO NIPPON SANSO CORPORATION, Japan; *Yuma Terauchi,* Tokyo University of Agriculture and Technology, Japan; *Tomohiro Yamaguchi,* Kogakuin University, Japan; *Masataka Higashiwaki,* Osaka Metropolitan University/NICT, Japan; *Yuzaburo Ban,* TAIYO NIPPON SANSO ATI CORPORATION, Japan; *Yoshinao Kumagai,* Tokyo University of Agriculture and Technology, Japan; *Tohru Honda,* Kogakuin University, Japan	
11:30am	**IWGO-ThM2-43** Formation and Stabilization of Ga Vacancies in β-$(Al,Ga)_2O_3$: Effects of Al-alloying, Si-doping, and Proton Irradiation, ***Iuliia Zhelezova (Student),*** *Ilja Makkonen,* University of Helsinki, Finland; *Zbigniew Galazka,* Leibniz-Institut für Kristallzüchtung, Germany; *Filip Tuomisto,* University of Helsinki, Finland	
11:45am	**IWGO-ThM2-46** Nitrogen-Doped (AlGa)2O3/n-Ga2O3 Junctions Grown by Plasma-Assisted Molecular Beam Epitaxy, ***Kohki Tsujimoto (Student),*** *Toshiki Nakaoka, Yusuke Teramura, Shoma Takeda, Satoko Honda, Masataka Higashiwaki,* Osaka Metropolitan University, Japan	

Friday Morning, August 7, 2026

Room ESJ 0202

7:15am	**BREAKFAST**	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-FrM1** **Plenary Session III** **Moderators:** **Shizuo Fujita**, Kyoto University, Japan, **Hongping Zhao**, The Ohio State University
8:00am	**INVITED: IWGO-FrM1-10** **PLENARY:** Scaling Ga_2O_3 Power Electronics: From 10 kV Devices to Megawatt Modules, ***Yuhao Zhang,*** The University of Hong Kong	
8:45am	**INVITED: IWGO-FrM1-19** Formation of High-Quality SiO_2/β-Ga_2O_3 MOS Structures: Design and Optimization of Post-Annealing Processes, ***Heiji Watanabe****, Kensei Maeda, Masahiro Hara, Takuma Kobayashi,* The University of Osaka, Japan	
9:10am	**IWGO-FrM1-24** Quaternary (AlxScyGa1−x−y)2O3 for Lattice-Matched β-Ga2O3 Heterostructures, ***Kazuki Koreishi (Student)****,* Institute of Science Tokyo, Japan*; Kodai Niitsu,* National Institute for Materials Science, Japan*; Takuto Soma,* Tohoku University, Japan*; Kohei Yoshimatsu, Akira Ohtomo,* Institute of Science Tokyo, Japan	
9:25am	**IWGO-FrM1-27** Characterization and Light Emission of CBLs with Varying Nitrogen Implantation Doses for β-Ga_2O_3 Devices, ***Kohei Ebihara****, Tetsuro Hayashida, Munetaka Noguchi, Rina Tanaka, Ryuji Sakai, Hiroshi Watanabe, Masaki Taya, Tatsuro Watahiki,* Mitsubishi Electric Corporation, Japan	
9:40am	**IWGO-FrM1-30** Development of Surface Preparation Methods for Insulating and Conductive, Miscut (100) β-Ga_2O_3 Substrates, ***Robert Lavelle****, Luke Lyle, Benjamin Dutton, Connor Beakes, Eric Welp, Scott Pistner, Andrew Balog,* Penn State University*; Drew Haven, David Joyce,* Luxium Solutions*; Nasim Alem, Joan Redwing, David Snyder,* Penn State University	
9:55am	**IWGO-FrM1-33** Analysis of Packaged Ga_2O_3 Schottky Barrier Diodes (SBDs) for AC Rectification at Industrial Voltages, ***Jeremiah Williams****,* KBR Inc.*; Nolan Hendricks, Joshua Piel,* AFRL*; Zachary Weber,* Ohio State Univ.*; Aaron Adams, Weisong Wang,* KBR Inc.*; Kyle Liddy, Daniel Dryden,* AFRL*; Takekazu Masui, Higuchi Mitsuhito,* NCT, Japan*; Ahmad Islam, Andrew Green,* AFRL	
10:10am	**BREAK & EXHIBITS**	
10:25am	**IWGO-FrM1-39** 2.2 kV NiO Based JTE β-Ga_2O_3 Schottky Barrier Diode with Improved Reliability under High-Temperature Storage Stress, ***Junpeng Wen (Student)****, Xuanze Zhou, Guangwei Xu, Shibing Long,* University of Science and Technology of China	
10:40am	**IWGO-FrM1-42** >1 GW/cm^2 β-Ga_2O_3 NiO_x Heterojunction Diodes on MOCVD-Grown (110) and (010) Epilayers, ***Carl Peterson (Student)****, Yizheng Liu, Chinmoy Nath Saha,* University of California Santa Barbara*; Jacob H. Leach,* Kyma Technologies Inc.*; James S. Speck, Sriram Krishnamoorthy,* University of California Santa Barbara	
10:55am	**IWGO-FrM2-45** Heavy-Ion Microprobe Induced Parasitic Channel in Ga2O3 MOSFETs, ***Adam Neal****,* Air Force Research Laboratory, Materials and Manufacturing Directorate, USA*; Daram Ramdin,* Core4ce*; Eric O'Quinn,* Univ. of Tennessee Knoxville*; Adam Charnas,* Air Force Research Lab,, Materials and Manufacturing Directorate, USA*; Kay-Obbe Voss,* GSI Helmholtzzentrum für Schwerionenforschung, Germany*; Cale Overstreet,* Univ. of Tennessee Knoxville*; Cameron Gorsak, Hari Nair,* Cornell Univ.*; Andrew Green,* Air Force Research Lab, Sensors Directorate*; Thaddeus Asel, Shin Mou,* Air Force Research Laboratory, Materials and Manufacturing Directorate, USA*; Maik Lang,* Univ. of Tennessee Knoxville	**International Workshop on Gallium Oxide and Related Materials (IWGO-6)** **Session IWGO-FrM2** **Advanced Device Scaling and Fabrication Techniques II** **Moderators:** **Samuel Graham**, University of Maryland College Park, **Marko Tadjer**, U.S. Naval Research Laboratory
11:10am	**IWGO-FrM2-48** Achievement of SiO_2/β-Ga_2O_3 (001) MOS Interface with Low in Terface State Density by Employing ALD with O_3 as an Oxidant and Low-temperature (600°C) Post-deposition Annealing, ***Atsushi Tamura****, Hayama Imaida, Koji Kita,* University of Tokyo, Japan	
11:25am	**BREAK & EXHIBITS**	
11:40am	**INVITED: IWGO-FrM2-54** High-Performance β-Ga_2O_3 Vertical Diodes and FinFETs with High Electric Field Strength, ***Sriram Krishnamoorthy****,* University of California at Santa Barbara	
12:05pm	**IWGO-FrM2-59** Diffusion Suppression of Mg and High Performance β-Ga_2O_3 Current Blocking Layers by N+Mg Co-Doping Approach, ***Fenfen Fenda Florena****, Hironobu Miyamoto, Yuki Koishikawa, Hirofumi Shinohara, Kohei Sasaki, Akito Kuramata,* NCT, Japan	
12:20pm	**IWGO-FrM2-62** >3.3 kV Ga_2O_3 Monolithic Bidirectional Switch: Impact of NiO/Ga2O3 Interface Charges, *Yuan Qin,* Virginia Tech*;* ***Yuhao Zhang,*** The University of Hong Kong, China	
12:35pm	**IWGO-FrM2-65** Kilovolt Class β-Ga_2O_3 Split Gate Vertical FinFET for Reduced Gate Capacitance, ***Saurav Roy****,* North Carolina State University*; Chinmoy N. Saha, Yizheng Liu, Akhila Mattapalli, Carl Peterson, James S. Speck, Sriram Krishnamoorthy,* University of California Santa Barbara	
12:50pm	**Closing Remarks**	

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